

POWER OF ATTORNEY

Applicants: Jingyi Bai, Weimin Li and William S. Budge

Application No.: _____ Filed: _____

Entitled: **METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN SEMICONDUCTOR LAYERS**

CERTIFICATE UNDER 37 CFR 3.73(b)

Micron Technology, Inc., a corporation of the State of Delaware, with a place of business at 8000 S. Federal Way, Boise, ID 83706-9632 certifies that it is the assignee of the entire right, title and interest in the patent application identified above by virtue of either:

A. ☒ An assignment from the inventor(s) of the patent application identified above, a copy of which is attached.

OR

B. ☐ A chain of title from the inventor(s), of the patent application identified above, to the current assignee as shown below:

1. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
Reel _____ Frame _____, or for which a copy thereof is attached.
2. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
Reel _____ Frame _____, or for which a copy thereof is attached.
3. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
Reel _____ Frame _____, or for which a copy thereof is attached.

☐ Additional documents in the chain of title are listed on a supplemental sheet.

☐ Copies of assignments or other documents in the chain of title are attached.

The undersigned has reviewed all the documents in the chain of title of the patent application identified above and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the assignee.

Micron Technology , Inc. hereby appoints the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

Richard A. Killworth	Reg. No. 26,397
James F. Gottman	Reg. No. 27,262
Timothy W. Hagan	Reg. No. 29,001
James E. Beyer	Reg. No. 39,564
Susan M. Luna	Reg. No. 38,769
Patricia L. Prior	Reg. No. 33,758
William A. Jividen	Reg. No. 42,695
Thomas E. Lees	Reg. No. 46,867
John D. Reed	Reg. No. 46,506
Brian L. Smiler	Reg. No. 46,458
Joan N. Williams	Reg. No. 52,364
Michael L. Lynch	Reg. No. 30,871
Charles B. Brantley, II.	Reg. No. 38,086

Address all telephone calls to (937) 223-2050. Address all correspondence to: KILLWORTH, GOTTMAN, HAGAN & SCHAEFF, L.L.P., One Dayton Centre, One South Main Street, Suite 500, Dayton, Ohio 45402-2023.

Micron Technology, Inc. hereby declares that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Date: _____

Name: Michael L. Lynch

Title: Chief Patent Counsel

Signature: _____

DECLARATION

As a below named inventor, I/we hereby declare that:

My residence, post office address and citizenship are as stated below next to my name; that

I/we verily believe I am the original and first inventor(s) of the invention entitled: **METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN SEMICONDUCTOR LAYERS** (MIO 0109 PA/02-1541), described and claimed

 X in the attached specification;
 in the specification filed , as U.S. Application Serial No.
 , and as amended .

I/we hereby authorize the attorney(s) and/or agent(s) appointed herein to indicate above whether the invention is described and claimed in an attached specification and to provide the Filing Date and Serial No. of the corresponding U.S. Application, if previously filed.

I/we hereby state that I/we have reviewed and understand the contents of the above identified specification, including the claims as filed and as amended by any amendment referred to above.

I/we acknowledge the duty to disclose to the Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56(a).

I/we further declare that all statements made herein of my/our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under §1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Full name of sole or first Inventor: **Jingyi Bai**

Inventor's signature _____

Date: _____

Residence: 3777 Gekeler Lane, Apt. 140
Boise, ID 83706

Citizenship: P.R. China

Post Office Address: c/o Micron Technology, Inc.
8000 S. Federal Way
Boise, ID 83706-9632

Full name of second Inventor: **Weimin Li**

Inventor's signature _____

Date: _____

Residence: 5513 E. Quartersawn St.
Boise, ID 83716

Citizenship: China

Post Office Address: c/o Micron Technology, Inc.
8000 S. Federal Way
Boise, ID 83706-9632

Full name of third Inventor: **William S. Budge**

Inventor's signature _____

Date: _____

Residence: 404 Cascade Ave.
Homedale, ID 83628

Citizenship: U.S.A.

Post Office Address: c/o Micron Technology, Inc.
8000 S. Federal Way
Boise, ID 83706-9632